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Silicon Carbide Schottky Diode

1200 V, 50 A

FFSH50120A

Description

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size & cost.

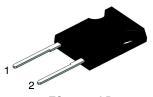
Features

- Max Junction Temperature 175°C
- Avalanche Rated 441 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery/No Forward Recovery
- This Device is Pb–Free, Halogen Free/BFR Free and RoHS Compliant

Applications

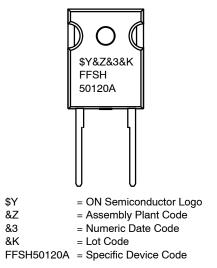
- General Purpose
- SMPS, Solar Inverter, UPS
- Power Switching Circuits





TO-247-2LD CASE 340CL

MARKING DIAGRAM



ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

Symbol	Parameter	Value	Unit		
V _{RRM}	Peak Repetitive Reverse Voltage	1200	V		
E _{AS}	Single Pulse Avalanche Energy (Note 1)	441	mJ		
١ _F	Continuous Rectified Forward Current @ T _C < 155°C		50	А	
	Continuous Rectified Forward Current @ T_C <	77	А		
I _{F, Max}	Non-Repetitive Peak Forward Surge Current	T _C = 25°C, 10 μs	1700	А	
		T _C = 150°C, 10 μs	1600	А	
I _{F,SM}	Non-Repetitive Forward Surge Current	Half-Sine Pulse, t _p = 8.3 ms	280	А	
I _{F,RM}	Repetitive Forward Surge Current	Half-Sine Pulse, t _p = 8.3 ms	85	А	
Ptot	Power Dissipation	$T_{\rm C} = 25^{\circ}{\rm C}$	736	W	
		T _C = 150°C	147	W	
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +175	°C	
	TO-247 Mounting Torque, M3 Screw		60 No		

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected. 1. E_{AS} of 441 mJ is based on starting $T_J = 25^{\circ}$ C, L = 0.5 mH, $I_{AS} = 42$ A, V = 50 V.

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
R _{0JC} Thermal Resistance, Junction to Case, Max		0.17	°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25° C unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Тур	Max	Unit
V _F	Forward Voltage	$I_{\rm F} = 50$ A, $T_{\rm C} = 25^{\circ}{\rm C}$	-	1.45	1.75	V
		I _F = 50 A, T _C = 125°C	-	1.7	2.0	
		I _F = 50 A, T _C = 175°C	-	2.0	2.4	1
I _R	Reverse Current	$V_{\rm R}$ = 1200 V, $T_{\rm C}$ = 25°C	-	-	200	μΑ
		V_{R} = 1200 V, T_{C} = 125°C	-	-	300	
		V_{R} = 1200 V, T_{C} = 175°C	-	-	400	
Q _C	Total Capacitive Charge	V = 800 V	-	252	-	nC
С	Total Capacitance	V _R = 1 V, f = 100 kHz	-	2560	-	pF
		V _R = 400 V, f = 100 kHz	-	234	-	
		V _R = 800 V, f = 100 kHz	-	190	-	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ORDERING INFORMATION

Part Number	Top Marking	Package	Shipping
FFSH50120A	FFSH50120A	TO-247-2LD	30 Units / Tube

TYPICAL CHARACTERISTICS

 $(T_J = 25^{\circ}C \text{ unless otherwise noted})$

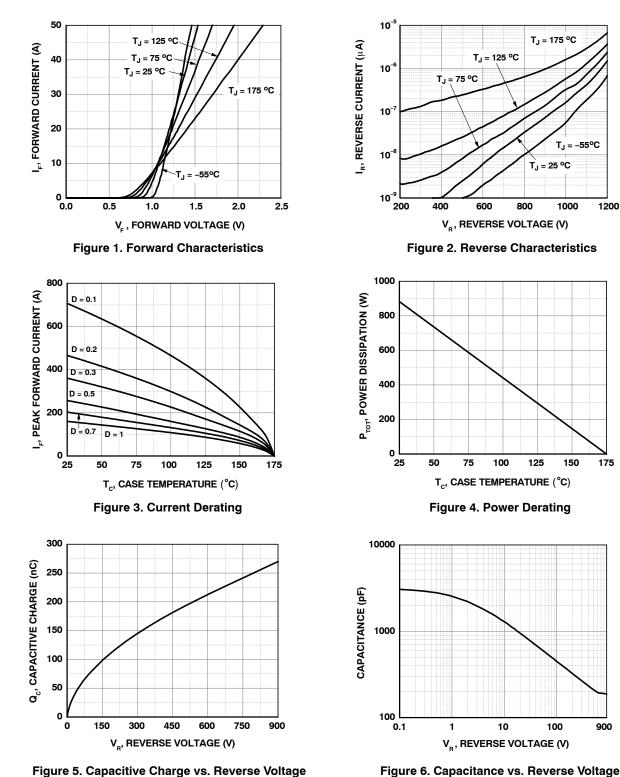
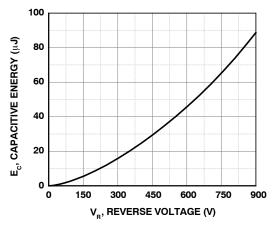


Figure 6. Capacitance vs. Reverse Voltage

TYPICAL CHARACTERISTICS

(T_J = 25° C unless otherwise noted)





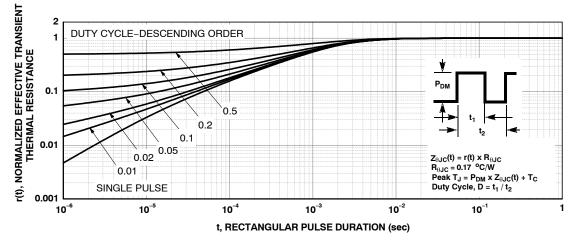


Figure 8. Junction-to-Case Transient Thermal Response Curve

TEST CIRCUIT AND WAVEFORMS

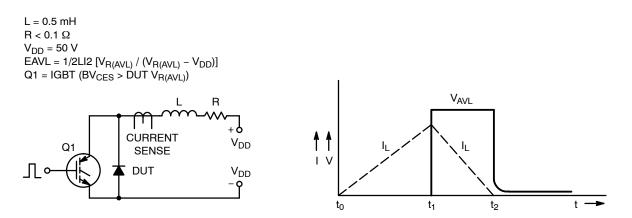


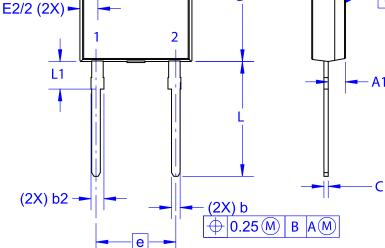
Figure 9. Unclamped Inductive Switching Test Circuit & Waveform

F

А

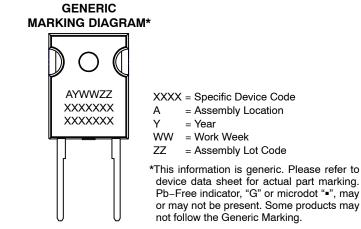
E2

TO-247-2LD CASE 340CL **ISSUE A** DATE 03 DEC 2019 Α ØP -A2 Q S D В E1 1



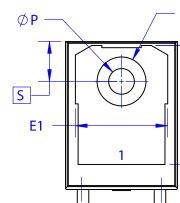
NOTES: UNLESS OTHERWISE SPECIFIED.

- A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DRAWING CONFORMS TO ASME Y14.5 2009. D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
- E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.



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DIM	MILLIMETERS			
DIN	MIN	NOM	MAX	
Α	4.58	4.70	4.82	
A1	2.29	2.40	2.66	
A2	1.30	1.50	1.70	
b	1.17	1.26	1.35	
b2	1.53	1.65	1.77	
С	0.51	0.61	0.71	
D	20.32	20.57	20.82	
D1	16.37	16.57	16.77	
D2	0.51	0.93	1.35	
E	15.37	15.62	15.87	
E1	12.81	2	~	
E2	4.96	5.08	5.20	
e	~	11.12	~	
L	15.75	16.00	16.25	
L1	3.69	3.81	3.93	
ØР	3.51	3.58	3.65	
Ø P 1	6.61	6.73	6.85	
Q	5.34	5.46	5.58	
S	5.34	5.46	5.58	

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D2

D1

Ø**P**1

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